

Amendments to the Specification:

*Please delete the heading before the title:*

~~Description~~

*Please amend the title to read as:*

RADIATION EMITTING SEMI-CONDUCTOR ELEMENT

Please insert the following paragraph after the title:

CROSS-REFERENCE TO RELATED APPLICATIONS

This application is the National Stage of International Application No. PCT/DE2004/001708, filed July 30, 2004, which claims the benefit of German Patent Applications Serial No. 103 39 983.6, filed on August 29, 2003, and Serial No. 103 46 605.3, filed on October 7, 2003. The contents of all applications are hereby incorporated by reference in their entireties.

*Please insert the following subheading immediately prior to the paragraph on page 1 beginning "The invention concerns...":*

FIELD OF THE INVENTION

*Please delete the second full paragraph on page 1, which starts with "This patent application claims..."*

*Please insert the following subheading immediately prior to the paragraph on page 1 beginning "In radiation-emitting semiconductor...":*

BACKGROUND OF THE INVENTION

*Please insert the following subheading immediately prior to the paragraph on page 2 beginning "The object of the present invention ...":*

SUMMARY OF THE INVENTION

*Please delete the fifth full paragraph on page 2, which starts with "This object is achieved by ..."*

*Please amend the paragraph beginning at page 9, which starts with "Particularly preferably, the ...":*

Particularly preferably, the outlined method is used to produce the semiconductor components described in ~~Claim 1 and the dependent claims~~ above.

*Please insert the following subheading immediately prior to the paragraph on page 9 beginning "Further features, advantages ...":*

BRIEF DESCRIPTION OF THE DRAWINGS

*Please insert the following subheading immediately prior to the paragraph on page 10 beginning "Figure 1 is a schematic ...":*

DETAILED DESCRIPTION OF THE PREFERRED EMBODIMENTS

*Please amend the last paragraph on page 11 as follows:*

Moreover, disposed on second current spreading layer 10 is a contact surface 13 for electrical contacting, which on its side facing semiconductor layer sequence 4 can be reflective (not explicitly illustrated) with respect to the radiation generated in the active zone 7. Contact surface 13 has a smaller lateral extent than current spreading layers 3, 10 and/or semiconductor layer sequence 4. Absorption of the generated radiation in contact surface 13 is reduced due to the fact that increased radiation generation is prevented in the region of active zone 7 that is shaded by the absorptive contact surface 13. Mirror-coating the underside of contact surface 13